

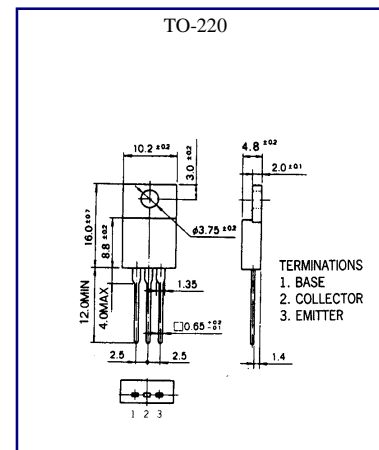


## TIP42 SERIRES (TIP42/42A/42B/42C)

PNP EPITAXIAL SILICON TRANSISTOR

### MEDIUM POWER LINEAR SWITCHING APPLICATIONS

●Complementary to TIP41/41A/41B/41C



### ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage :TIP41	V <sub>CB0</sub>	-40	V
:TIP41A		-60	V
:TIP41B		-80	V
:TIP41C		-100	V
Collector-Emitter Voltage :TIP41	V <sub>CEO</sub>	-40	V
:TIP41A		-60	V
:TIP41B		-80	V
:TIP41C		-100	V
Emitter-Base voltage	V <sub>EBO</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-6	A
Collector Current (Pulse)	I <sub>C</sub>	-10	A
Base Current (DC)	I <sub>B</sub>	-2	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	65	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C

Wing Shing Computer Components Co., (H.K.)Ltd.  
Homepage: <http://www.wingshing.com>

Tel:(852)2341 9276 Fax:(852)2797 8153  
E-mail: wsccltd@hkstar.com

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage :TIP41 :TIP41A :TIP41B :TIP41C	BV <sub>CEO(SUS)</sub>	I <sub>C</sub> =-30mA, I <sub>B</sub> =0	-40 -600 -80 -100			V V V V
Collector Cutoff Current :TIP41/41A :TIP41B/41C	I <sub>CEO</sub>	V <sub>CE</sub> = -30V, I <sub>B</sub> =0 V <sub>CE</sub> = -60V, I <sub>B</sub> =0			-0.7 -0.7	mA mA
Collector Cutoff Current :TIP41 :TIP41A :TIP41B :TIP41C	I <sub>CES</sub>	V <sub>CE</sub> = -40V, V <sub>EB</sub> = 0 V <sub>CE</sub> = 60V, V <sub>EB</sub> = 0 V <sub>CE</sub> = -80V, V <sub>EB</sub> = 0 V <sub>CE</sub> = -100V, V <sub>EB</sub> = 0			-400 -400 -400 -400	μA μA μA μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-1	mA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -4V, I <sub>C</sub> =- 0.3A	30 15		75	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>CE</sub> = -4V, I <sub>C</sub> =-3A			-1.5	V
Base- Emitter On Voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =-6A, I <sub>B</sub> =-600mA			-2.0	V
Current Gain Bandwith Product	f <sub>T</sub>	V <sub>CE</sub> = -4V, I <sub>C</sub> =-6A V <sub>CE</sub> = - 10V, I <sub>C</sub> =500mA f=1MHZ	3.0			MHZ